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<input type="checkbox"/>	L6	L5 not L4	27763
<input type="checkbox"/>	L5	((critical adj dimension) or CD or (gate with width) or (line with width)) same (wavelength or photolithograp\$8 or lithograp\$8)	27980
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<input type="checkbox"/>	L4	(L1 or L2 or L3) and ((critical adj dimension) or CD or (gate with width) or (line with width)) and (photolithograp\$8 or lithograp\$8)	437
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IEE CNF	IEE Conference Proceeding
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Select Article Information

- ☐ 1. **Patterning sub-30-nm MOSFET gate with I-line lithography**
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